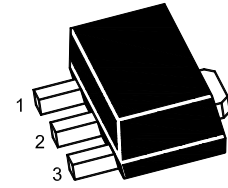


2SD2150U

NPN Silicon Epitaxial Planar Power Transistor

Features

- Low frequency



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	3	A
Peak Collector Current, Pulsed ¹⁾	I_{CM}	5	A
Total Power Dissipation	P_{tot}	0.5 ²⁾ 2 ³⁾	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

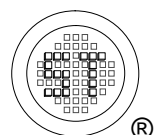
Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	250 ²⁾ 62.5 ³⁾	$^\circ\text{C/W}$

¹⁾ Single pulse $P_w = 10$ ms

²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

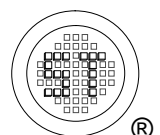
³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.



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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 100\text{ mA}$	Current Gain Group R	h_{FE}	180	-	390	-
	S	h_{FE}	270	-	560	-
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	-	100	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	100	nA	
Collector Base Breakdown Voltage at $I_C = 50\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	-	V	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 50\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 100\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $V_{CE} = 2\text{ V}$, $-I_E = 500\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	290	-	MHz	
Collector Output Capacitance at $V_{CE} = 10\text{ V}$, $I_E = 0\text{ A}$, $f = 1\text{ MHz}$	C_{ob}	-	20	-	pF	



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Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

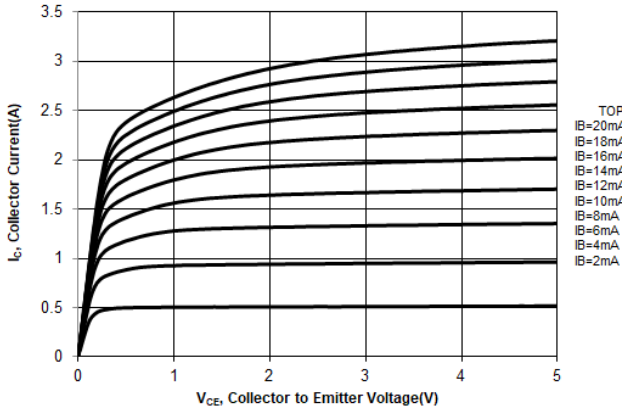


Fig. 2 Collector Current vs. Base to Emitter Voltage

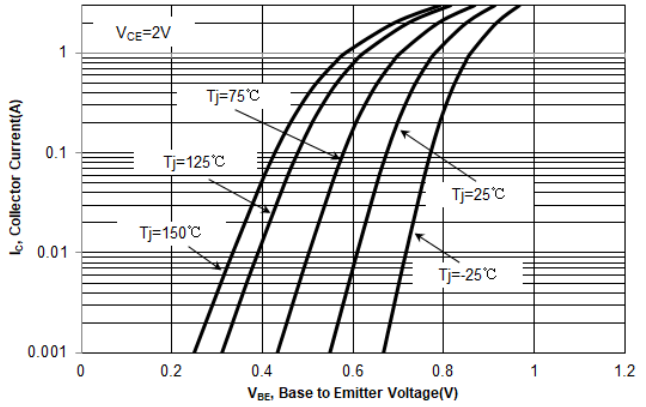


Fig. 3 DC Current Gain vs. Collector Current

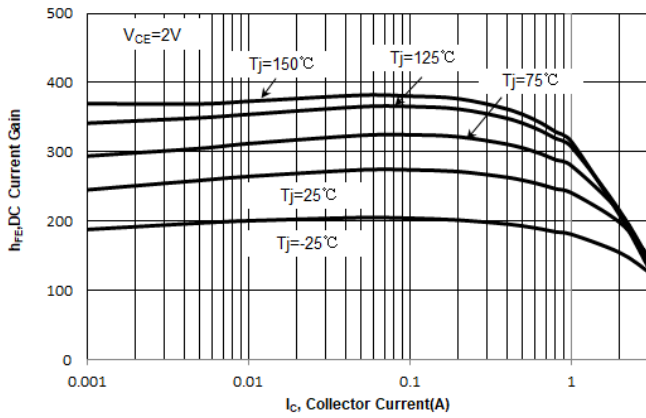
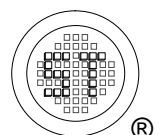
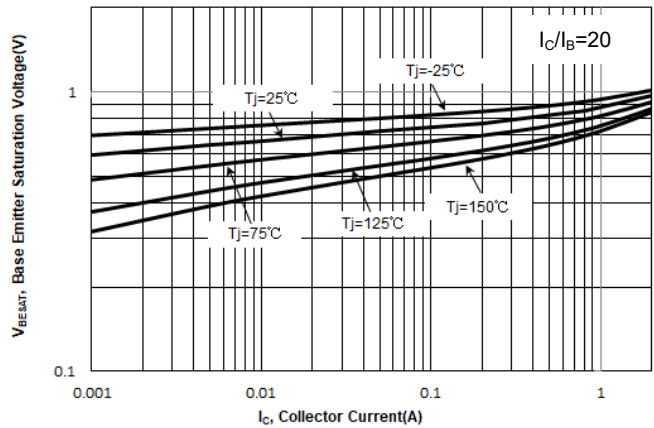


Fig. 4 V_{BESAT} vs. Collector Current



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Electrical Characteristics Curves

Fig. 5 V_{CESAT} vs. Collector Current

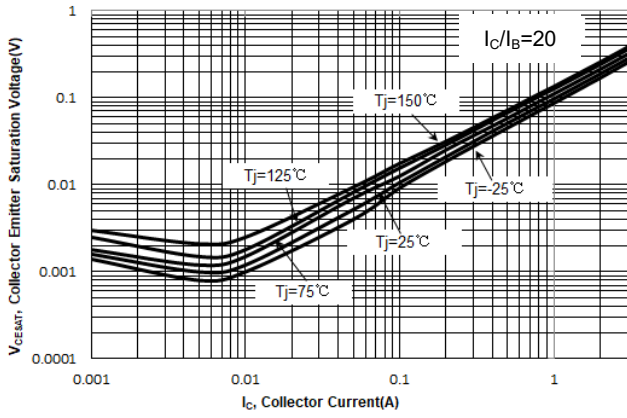


Fig. 6 Output Capacitance

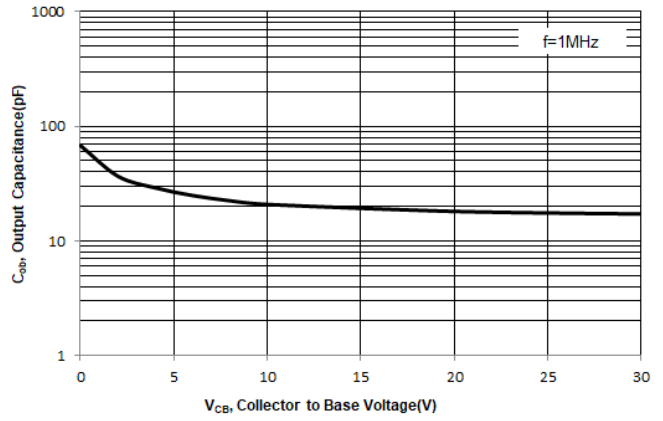
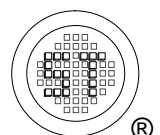
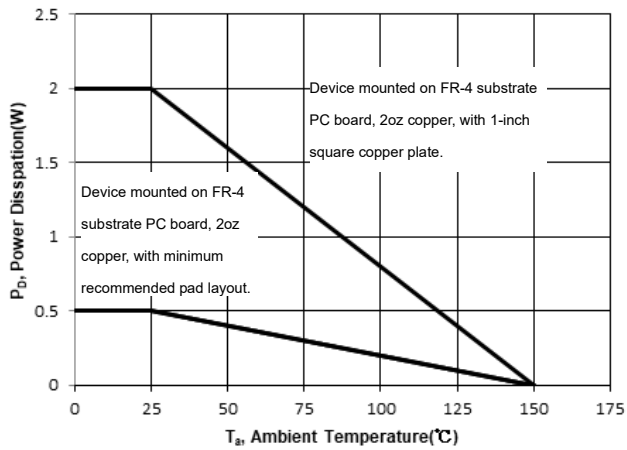


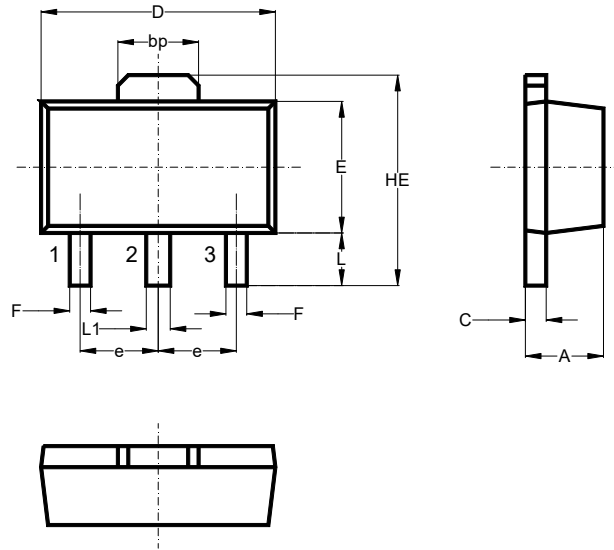
Fig. 7 Power Derating Curve



2SD2150U

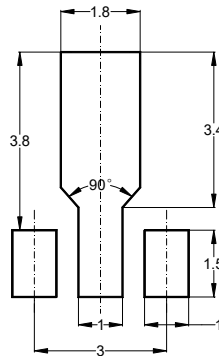
Package Outline (Dimensions in mm)

SOT-89



Unit	A	bp	C	D	E	F	HE	e	L	L1
mm	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

Marking information

" 2SD2150*U " = Part No. (" * " = HFE grouping Code)

"YM" = Date Code Marking

"Y" = Year

"M" = Month

Font type: Arial

